

September 2010

FAN7389 3-Phase Half-Bridge Gate-Drive IC

Features

- Floating Channel for Bootstrap Operation to +600V
- Typically 350mA/650mA Sourcing/Sinking Current Driving Capability for All Channels
- Extended Allowable Negative V_S Swing to -9.8V for Signal Propagation at V_{DD}=V_{BS}=15V
- Output In-Phase with Input Signal
- Over-Current Shutdown Turns off All Six Drivers
- Matched Propagation Delay for All Channels
- 3.3V and 5V Input Logic Compatible
- Adjustable Fault-Clear Timing
- Built-in Advanced Input Filter
- Built-in Shoot-Through Prevention Logic
- Built-in Soft Turn-Off Function
- Common-Mode dv/dt Noise Canceling Circuit
- Built-in UVLO Functions for All Channels

Applications

- 3-Phase Motor Inverter Driver
- Air Conditioners
- Washing Machines
- General-Purpose Three-Phase Inverters

Description

The FAN7389 is a monolithic three-phase half-bridge gate-drive IC designed for high-voltage, high-speed driving MOSFETs and IGBTs operating up to +600V.

Fairchild's high-voltage process and common-mode noise canceling technique provide stable operation of high-side drivers under high-dv/dt noise circumstances.

An advanced level-shift circuit allows high-side gate driver operation up to $V_S = -9.8V$ (typical) for $V_{BS} = 15V$.

The protection functions include under-voltage lockout and inverter over-current trip with an automatic fault-clear function.

Over-current protection that terminates all six outputs can be derived from an external current-sense resistor. An open-drain fault signal is provided to indicate that an over-current or under-voltage shutdown has occurred.

The UVLO circuits prevent malfunction when V_{DD} and V_{BS} are lower than the specified threshold voltage.

Output drivers typically source and sink 350mA and 650mA, respectively; which is suitable for three-phase half-bridge applications in motor drive systems.

24-SOIC



Ordering Information

Part Number	Package	Operating Temperature	Packing Method	
FAN7389M ⁽¹⁾	24 SOD	24-SOP -40 to +125°C		
FAN7389MX ⁽¹⁾	- 24-SOP	-40 to +125 C	Tape & Reel	

Note:

These devices passed wave soldering test by JESD22A-111.

Typical Application Diagram V_{DD} V_{MOTOR} UU HO1 (23 HIN2 3-Phase WU BLDC Motor Controller UL HIN3 V_{B2} LIN1 HO2 (20) V_{S2} (19 LIN2 LIN3 V_{B3} (18) FO ноз (17 3-Phase Inverter CONTROL cs V_{S3} (16) (10) EN LO1 (15) RCIN LO2 (14) C_{RCIN} LO3 (13) 12) COM

Figure 1. 3-Phase BLDC Motor Drive Application

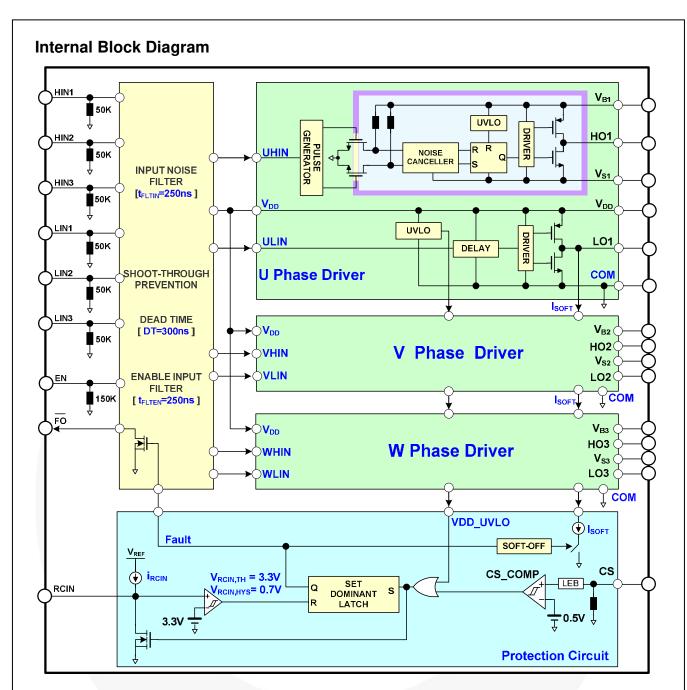


Figure 2. Functional Block Diagram

Pin Configuration

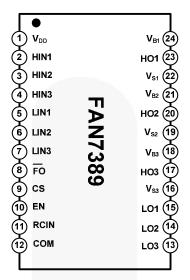


Figure 3. Pin Configuration

Pin Definitions

Pin#	Name	Description	
1	V_{DD}	Logic and low-side gate drivers power supply voltage	
2	HIN1	Logic Input 1 for high-side gate 1 driver	
3	HIN2	Logic Input 2 for high-side gate 2 driver	
4	HIN3	Logic Input 3 for high-side gate 3 driver	
5	LIN1	Logic Input 1 for low-side gate 1 driver	
6	LIN2	Logic Input 2 for low-side gate 2 driver	
7	LIN3	Logic Input 3 for low-side gate 3 driver	
8	FO	Fault output with open-drain (indicates over-current and low-side under-voltage)	
9	CS	Analog input for over-current shutdown	
10	EN	Logic input for shutdown functionality	
11	RCIN	An external RC network input used to define the fault-clear delay	
12	COM	Low-side driver return	
13	LO3	Low-side gate driver 3 output	
14	LO2	Low-side gate driver 2 output	
15	LO1	Low-side gate driver 1 output	
16	V _{S3}	High-side driver 3 floating supply offset voltage	
17	HO3	High-side driver 3 gate driver output	
18	V _{B3}	High-side driver 3 floating supply	
19	V _{S2}	High-side driver 2 floating supply offset voltage	
20	HO2	High-side driver 2 gate driver output	
21	V _{B2}	High-side driver 2 floating supply	
22	V _{S1}	High-side driver 1 floating supply offset voltage	
23	HO1	High-side driver 1 gate driver output	
24	V _{B1}	High-side driver 1 floating supply	

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A=25^{\circ}C$, unless otherwise specified.

Symbol	Parameter	Min.	Max.	Unit
Vs	High-Side Floating Offset Voltage	V _{B1,2,3} -25	V _{B1,2,3} +0.3	V
V _B	High-Side Floating Supply Voltage	-0.3	625	V
V _{DD}	Low-side and logic-fixed supply voltage	-0.3	25	V
V _{HO}	High-Side Floating Output Voltage V _{HO1,2,3}	V _{S1,2,3} -0.3	V _{B1,2,3} +0.3	V
V _{LO}	Low-Side Floating Output Voltage V _{LO1,2,3}	-0.3	V _{DD} +0.3	V
V _{IN}	Input Voltage (HINx, LINx, CS, and EN)	-0.3	5.5	V
V _{FO}	Fault Output Voltage (FO)	-0.3	V _{DD} +0.3	V
PW _{HIN}	High-Side Input Pulse Width	500		ns
dV _S /dt	Allowable Offset Voltage Slew Rate		±50	V/ns
P _D	Power Dissipation ^(2,3,4)		1.4	W
θ _{JA}	Thermal Resistance		70	°C/W
TJ	Junction Temperature		150	°C
T _{STG}	Storage Temperature	-55	150	°C

Notes:

- 2. Mounted on 76.2 x 114.3 x 1.6mm PCB (FR-4 glass epoxy material).
- Refer to the following standards: JESD51-2: Integral circuits thermal test method environmental conditions - natural convection JESD51-3: Low effective thermal conductivity test board for leaded surface-mount packages.
- Do not exceed P_D under any circumstances.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Min.	Max.	Unit
V _{B1,2,3}	High-Side Floating Supply Voltage	V _{S1,2,3} +10	V _{S1,2,3} +20	V
V _{S1,2,3}	High-Side Floating Supply Offset Voltage	6-V _{DD}	600	V
V_{DD}	Low-Side and Logic Fixed Supply Voltage	10	20	V
V _{HO1,2,3}	High-Side Output Voltage	V _{S1,2,3}	V _{B1,2,3}	V
V _{LO1,2,3}	Low-Side Output Voltage	COM	V_{DD}	V
V_{FO}	Fault Output Voltage (FO)	V_{DD}	V	
V _{CS}	V _{CS} Current-Sense Pin Input Voltage			V
V _{IN}	Logic Input Voltage (HIN1,2,3 and LIN1,2,3)		5	V
T _A	Ambient Temperature	-40	+125	°C

Electrical Characteristics

 V_{BIAS} (V_{DD} , $V_{BS1,2,3}$) = 15.0V and T_A = 25°C unless otherwise specified. The V_{IN} and I_{IN} parameters are referenced to COM and are applicable to all six channels. The V_O and I_O parameters are referenced to $V_{S1,2,3}$ and COM and are applicable to the respective output leads: HO1,2,3 and LO1,2,3. The V_{DDUV} parameters are referenced to COM. The V_{BSUV} parameters are referenced to $V_{S1,2,3}$.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Low-Side	Power Supply Section					
I_{QDD}	Quiescent V _{DD} Supply Current	V _{LIN1,2,3} =0V or 5V, EN=0V		200		μΑ
I _{PDD}	Operating V _{DD} Supply Current	f _{LIN1,2,3} =20kHz, rms Value		400		μΑ
$V_{\text{DDUV+}}$	V _{DD} Supply Under-Voltage Positive-Going Threshold	V _{DD} =Sweep	7.5	8.5	9.3	٧
V_{DDUV}	V _{DD} Supply Under-Voltage Negative-Going Threshold	V _{DD} =Sweep	7.0	8.0	8.7	V
V _{DDHYS}	V _{DD} Supply Under-Voltage Lockout Hysteresis	V _{DD} =Sweep		0.5		V
Bootstrap	oped Power Supply Section					
V _{BSUV+}	V _{BS} Supply Under-Voltage Positive-Going Threshold	V _{BS1,2,3} =Sweep	7.5	8.5	9.3	V
V _{BSUV} -	V _{BS} Supply Under-Voltage Negative-Going Threshold	V _{BS1,2,3} =Sweep	7.0	8.0	8.7	V
V _{BSHYS}	V _{BS} Supply Under-Voltage Lockout Hysteresis	V _{BS1,2,3} =Sweep		0.5		V
I _{LK}	Offset Supply Leakage Current	V _{B1,2,3} =V _{S1,2,3} =600V			10	μΑ
I _{QBS}	Quiescent V _{BS} Supply Current	V _{HIN1,2,3} =0V or 5V, EN=0V	10	50	80	μА
I _{PBS}	Operating V _{BS} Supply Current	f _{HIN1,2,3} =20kHz, rms Value	200	420	480	μА
Gate Driv	er Output Section					
V _{OH}	High-Level Output voltage, V _{BIAS} -V _O	I _O =0mA (No Load)			100	mV
V_{OL}	Low-Level Output voltage, Vo	I _O =0mA (No Load)			100	mV
I _{O+}	Output HIGH Short-Circuit Pulse Current ⁽⁵⁾	V _O =0V, V _{IN} =5V with PW≤10μs	250	350		mA
I _O -	Output LOW Short-Circuit Pulsed Current ⁽⁵⁾	V _O =15V, V _{IN} =0V with PW≤10μs	500	650		mA
V_S	Allowable Negative V _S Pin Voltage for HIN Signal Propagation to HO			-9.8	-7.0	V
Logic Inp	ut Section					,
V _{IH}	Logic "1" Input Voltage HIN1,2,3, LIN1,2,3		2.5			V
V _{IL}	Logic "0" Input Voltage HIN1,2,3, LIN1,2,3				0.8	V
I _{IN+}	Logic Input Bias Current (HO=LO=HIGH)	V _{IN} =5V		100		μА
I _{IN-}	Logic Input Bias Current (HO=LO=LOW)	V _{IN} =0V		/=	2	μА
R _{IN}	Logic Input Pull-Down Resistance			50		ΚΩ
Enable C	ontrol Section (EN)			•	VI	V
$V_{\text{EN+}}$	Enable Positive-Going Threshold Voltage		2.5			V
$V_{EN ext{-}}$	Enable Negative-Going Threshold Voltage				8.0	V
I _{EN+}	Logic Enable "1" Input Bias Current	V_{EN} =5V (Pull-Down=150KΩ)		33		μΑ
I _{EN-}	Logic Enable "0" Input Bias Current	V _{EN} =0V			2	μА

Continued on the following page...

Electrical Characteristics

 V_{BIAS} (V_{DD} , $V_{BS1,2,3}$) = 15.0V and T_A = 25°C unless otherwise specified. The V_{IN} and I_{IN} parameters are referenced to COM and are applicable to all six channels. The V_O and I_O parameters are referenced to $V_{S1,2,3}$ and COM and are applicable to the respective output leads: HO1,2,3 and LO1,2,3. The V_{DDUV} parameters are referenced to COM. The V_{BSUV} parameters are referenced to $V_{S1,2,3}$.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit		
Over-Cur	Over-Current Protection Section							
V _{CSTH+}	Over-Current Detect Positive Threshold ⁽⁵⁾		400	500	600	mV		
V _{CSTH} -	Over-Current Detect Negative Threshold ⁽⁵⁾			440		mV		
V _{CSHYS}	Over-Current Detect Hysteresis ⁽⁵⁾			60		mV		
I _{CSIN}	Short-Circuit Input Current	V _{CSIN} =1V	5	10	15	μΑ		
I _{SOFT}	Soft Turn-Off Sink Current		25	40	55	mA		
Fault Out	put Section							
V _{RCINTH+}	RCIN Positive-Going Threshold Voltage			3.3		V		
V _{RCINTH} -	RCIN Negative-Going Threshold Voltage			2.6		V		
V _{RCINHYS}	RCIN Hysteresis Voltage			0.7		V		
I _{RCIN}	RCIN Internal Current Source	C _{RCIN} =2nF	3	5	7	μΑ		
V_{FOL}	Fault Output Low Level Voltage	V _{CS} =1V, I _{FO} =1.5mA		0.2	0.5	V		
R _{DSRCIN}	RCIN On Resistance	I _{RCIN} =1.5mA	50	75	100	Ω		
R _{DSFO}	Fault Output On Resistance	I _{FO} =1.5mA	90	130	170	Ω		

Note:

Dynamic Electrical Characteristics

 T_A =25°C, V_{BIAS} (V_{DD} , $V_{BS1,2,3}$) = 15.0V, $V_{S1,2,3}$ = COM, and C_{Load} = 1000pF unless otherwise specified.

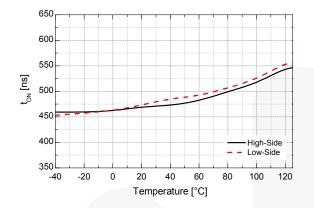
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
ton	Turn-On Propagation Delay	V _{LIN1,2,3} =V _{HIN1,2,3} =0V, V _{S1,2,3} =0V	350	500	650	ns
t _{OFF}	Turn-Off Propagation Delay	V _{LIN1,2,3} =V _{HIN1,2,3} =5V, V _{S1,2,3} =0V	350	500	650	ns
t_R	Turn-On Rise Time	V _{LIN1,2,3} =V _{HIN1,2,3} =0V	20	50	100	ns
t_{F}	Turn-Off Fall Time	V _{LIN1,2,3} =V _{HIN1,2,3} =5V	10	30	80	ns
t _{EN}	Enable LOW to Output Shutdown Delay		400	500	600	ns
tcsblt	CS Pin Leading-Edge Blanking Time ⁽⁶⁾		200	300	400	ns
t _{CSFO}	Time from CS Triggering to FO	From V _{CSC} =1V to FO Turn-Off		630	/	ns
t _{CSOFF}	Time from CS Triggering to All Gate Outputs Turn-Off	From V _{CSC} =1V to Starting Gate Turn-Off		640		ns
t _{FLT,IN}	Input Filtering Time ⁽⁷⁾ (HINx, LINx)		200	250	300	ns
	Input Filtering Time ⁽⁷⁾ (EN)		200	250	300	ns
t _{FLTCLR}	Fault-Clear Time	RCIN: C _{RCIN} =2nF		1.3		ms
DT	Dead Time		250	300	350	ns
MDT	Dead-Time Matching (All Six Channels)				50	ns
MT	Delay Matching (All Six Channels)				50	ns
PM	Output Pulse-Width Matching ^(6,8)	PW _{IN} > 1µs		50	100	ns

Notes:

- 6. These parameters are guaranteed by design.
- 7. The minimum width of the input pulse should exceed 500ns to ensure the filtering time of the input filter is exceeded.
- B. PM is defined as PW_{IN}-PW_{OUT},

^{5.} These parameters are guaranteed by design.

Typical Characteristics



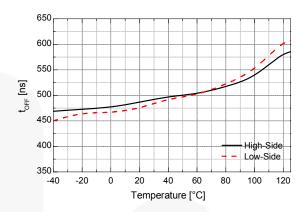


Figure 4. Turn-On Propagation Delay vs. Temperature

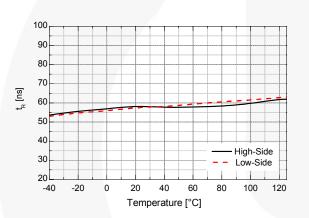


Figure 5. Turn-Off Propagation Delay vs. Temperature

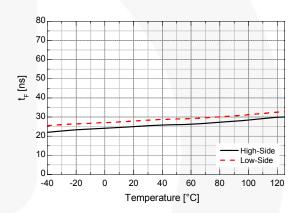


Figure 6. Turn-On Rise Time vs. Temperature

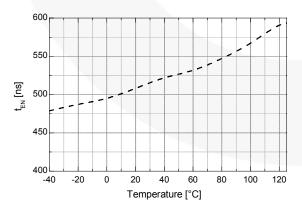


Figure 7. Turn-Off Fall Time vs. Temperature

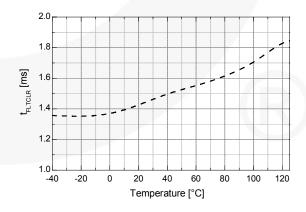
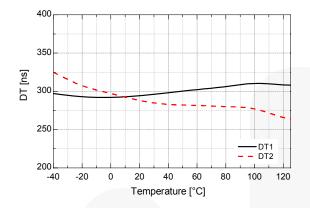


Figure 8. Enable LOW to Output Shutdown Delay vs. Temperature

Figure 9. Fault-Clear Time vs. Temperature



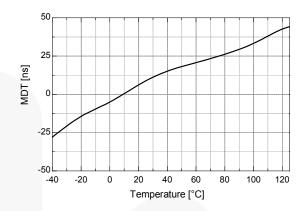
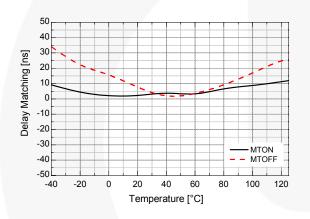


Figure 10. Dead Time vs. Temperature

Figure 11. Dead-Time Matching vs. Temperature



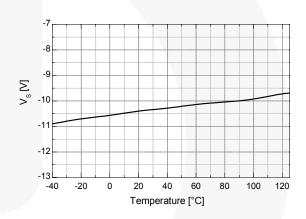
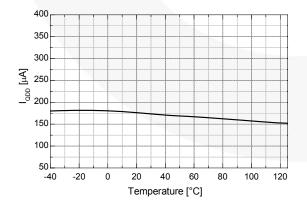


Figure 12. Delay Matching vs. Temperature



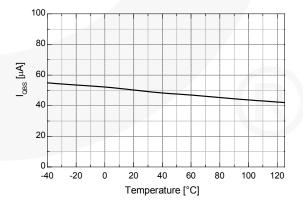
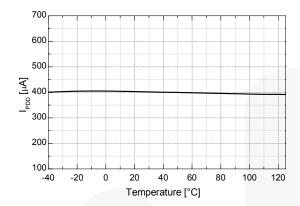


Figure 14. Quiescent V_{DD} Supply Current vs. Temperature

Figure 15. Quiescent V_{BS} Supply Current vs. Temperature



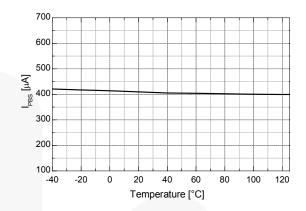


Figure 16. Operating V_{DD} Supply Current vs. Temperature

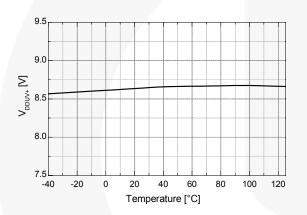


Figure 17. Operating V_{BS} Supply Current vs. Temperature

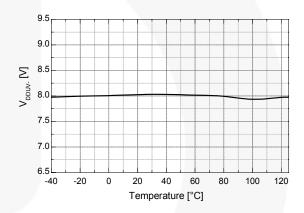


Figure 18.V_{DD} UVLO+ vs. Temperature

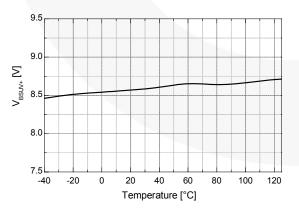


Figure 19.V_{DD} UVLO- vs. Temperature

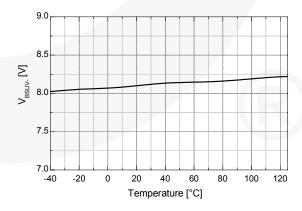
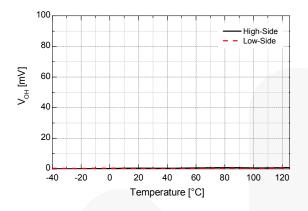


Figure 20.V_{BS} UVLO+ vs. Temperature

Figure 21.V_{BS} UVLO- vs. Temperature



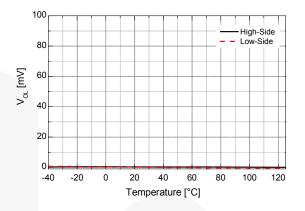
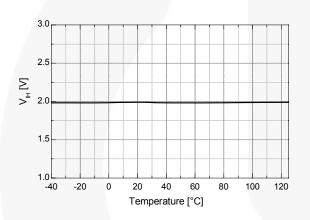


Figure 22. High-Level Output Voltage vs. Temperature Figure 23. Low-Level Output Voltage vs. Temperature



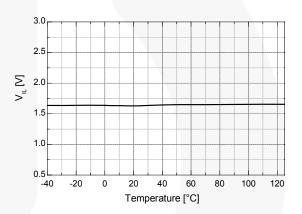
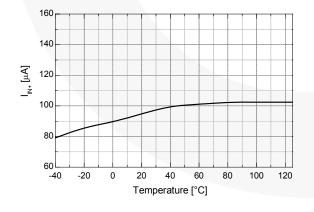


Figure 24.Logic HIGH Input Voltage vs. Temperature Figure 25.Logic LOW Input Voltage vs. Temperature



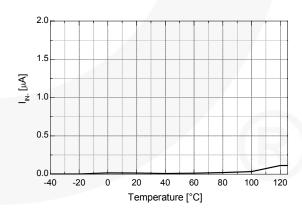
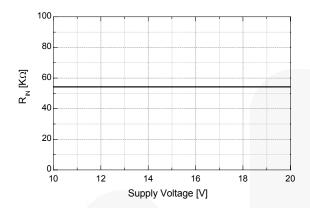


Figure 26.Logic Input HIGH Bias Current vs. Temperature

Figure 27.Logic Input LOW Bias Current vs. Temperature



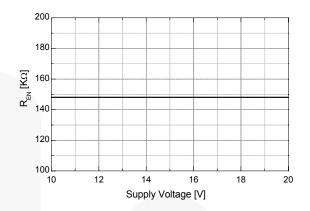


Figure 28. Input Pull-Down Resistance vs. Supply Voltage

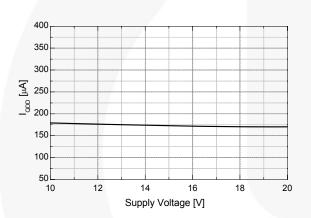


Figure 29.Enable Pin Pull-Down Resistance vs. Supply Voltage

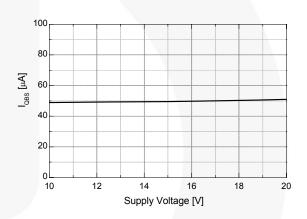


Figure 30. Quiescent V_{DD} Supply Current vs. Supply Voltage

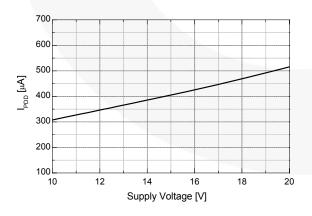


Figure 31. Quiescent V_{BS} Supply Current vs. Supply Voltage

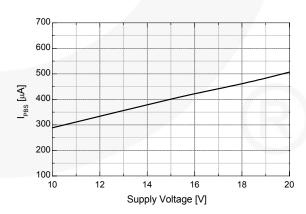


Figure 32. Operating V_{DD} Supply Current vs. Supply Voltage

Figure 33. Operating V_{BS} Supply Current vs. Supply Voltage

Switching Time Definitions

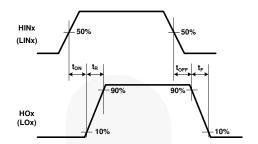


Figure 34. Switching Time Waveform Definitions

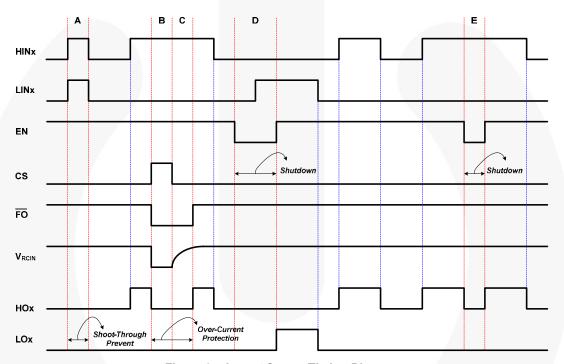


Figure 35. Input / Output Timing Diagram

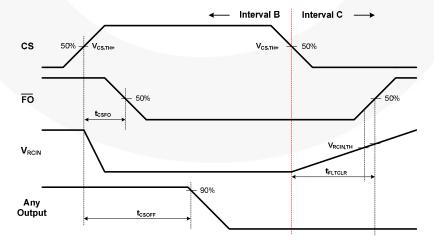


Figure 36. Detailed View of B and C Intervals During Over-Current Protection

Applications Information

1. Dead Time

Dead time is automatically inserted whenever the dead time of the external two input signals (between HINx and LINx signals) is shorter than internal fixed dead times (DT1 and DT2). Otherwise, external dead times larger than internal dead times are not modified by the gate driver and internal dead-time waveform definition is shown in Figure 37.

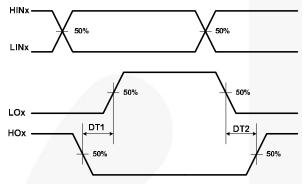


Figure 37.Internal Dead-Time Definitions

2. Protection Function

2.1 Fault Out (FO) and Under-Voltage Lockout

The high- and low-side drivers include under-voltage lockout (UVLO) protection circuitry that monitors the supply voltage for V_{DD} and V_{BS} independently. It can be designed to prevent malfunction when V_{DD} and V_{BS} are lower than the specified threshold voltage. Also, the UVLO hysteresis prevents chattering during power-supply transitions. Moreover, the fault signal (FO) goes to LOW state to operate reliably during power-on events, when the power supply (VDD) is below the under-voltage lockout high threshold voltage for the circuit (during $t_1 \sim t_2$). The UVLO circuit is not otherwise activated; shown Figure 38.

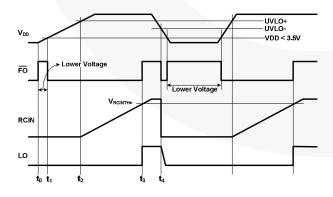


Figure 38. Waveforms for Under-Voltage Lockout

2.2 Shoot-Through Protection

The shoot-through protection circuitry prevents both high- and low-side switches from conducting at the same time, as shown Figure 39.

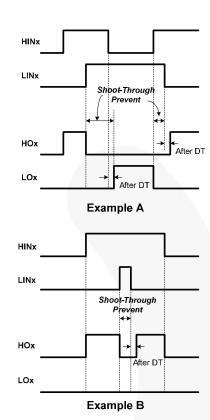


Figure 39. Shoot-Through Protection

2.3 Enable Input

When the \dot{EN} pin is in HIGH state, the gate driver operates normally. When a condition occurs that should shut down the gate driver, the EN pin should be LOW. The enable circuitry has an input filter; the minimum input duration is specified by $t_{FLT,IN}$ (typically 250ns).

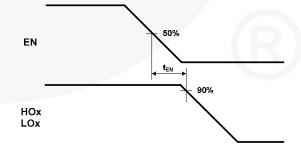


Figure 40. Output Enable Timing Waveform

2.4 Fault-Out (FO) and Over-Current Protection

FAN7389 provides an integrated fault output (\overline{FO}) and an adjustable fault-clear timer (t_{FLTCLR}) . There are two situations that cause the gate driver to report a fault via the FO pin. The first is an under-voltage condition of low-side gate driver supply voltage (V_{DD}) and the second is when the current-sense pin (CS) recognizes a fault. Once the fault condition occurs, the FO pin is internally pulled to COM, the fault-clear timer is activated, and all outputs (HO1,2,3) and LO1,2,3) of the gate driver are turned off. The fault output stays LOW until the fault condition has been removed and the fault-clear timer expires, the voltage on the FO pin returns to pull-up voltage.

The fault-clear time (t_{FLTCLR}) is determined by an internal current source (I_{RCIN} =5 μ A) and an external C_{RCIN} at the RCIN pin, as shown in this equation:

$$t_{FLTCLR} = \frac{C_{RCIN} \times V_{RCIN,TH}}{I_{RCIN}}[s]$$
 (1)

The $R_{\text{ON,RCIN}}$ of the MOSFET is a characteristic discharge curve with respect to the external capacitor C_{RCIN} . The time constant is defined by the external capacitor C_{RCIN} and the $R_{\text{ON,RCIN}}$ of the MOSFET.

The output of current-sense comparator (CS_COMP) passes a noise filter, which inhibits an over-current shutdown caused by parasitic voltage spikes of V_{CS} .

This corresponds to a voltage level at the comparator of V_{CSTH+} - V_{CSHYS} = 500mV - 60mV =440mV, where V_{CSHYS} =60mV is the hysteresis of the current comparator (CS COMP) as shown in Figure 41.

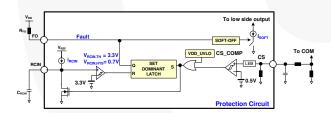


Figure 41. Over-Current Protection

Figure 42 shows the waveform definitions of RCIN, FO and the low-side driver, which uses a soft turn-off method when an under-voltage condition of the low-side gate driver supply voltage (V_{DD}) or the current-sense pin (CS) recognizes a fault. Once a fault condition occurs, the FO pin is internally pulled to COM and all outputs (HO1,2,3 and LO1,2,3) of the gate driver are turned off. Low-side outputs decline linearly by the internal sink current source (I_{SOFT} =40mA) for soft turn-off, as shown in Figure 42.

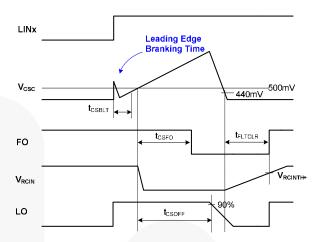


Figure 42.R_{CIN} and Fault-Clear Waveform Definition

3. Noise Filter

3.1 Input Noise Filter

Figure 43 shows the input noise filter method, which has symmetry duration between the input signal (t_{INPUT}) and the output signal (t_{OUTPUT}) and helps to reject noise spikes and short pulses. This input filter is applied to the HINx, LINx, and EN inputs. The upper pair of waveforms (Example A) shows an input signal duration (t_{INPUT}) much longer than input filter time (t_{FLTIN}) ; it is approximately the same duration between the input signal time (t_{INPUT}) and the output signal time (t_{OUTPUT}) . The lower pair of waveforms (Example B) shows an input signal time (t_{INPUT}) slightly longer than input filter time (t_{FLTIN}) ; it is approximately the same duration between input signal time (t_{INPUT}) and the output signal time (t_{OUTPUT}) .

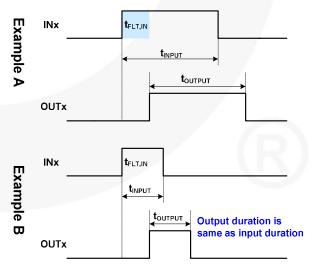


Figure 43.Input Noise Filter Definition

3.2. Short-Pulsed Input Noise Rejection Method

The input filter circuitry provides protection against short-pulsed input signals (HINx, LINx, and EN) on the input signal lines by applied noise signal.

If the input signal duration is less than input filter time $(t_{\text{FLT,IN}})$, the output does not change states.

Example A and B of the Figure 44 show the input and output waveforms with short-pulsed noise spikes with a duration less than input filter time; the output does not change states.

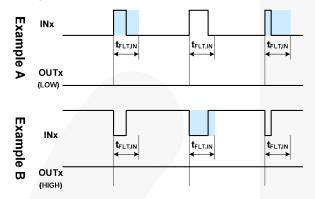


Figure 44. Noise Rejecting Input Filter Definition

Figure 45 shows the characteristics of the input filters while receiving narrow ON and OFF pulses. If input signal pulse duration, PW_{IN} , is less than input filter time, $t_{\text{FLT,IN}}$; the output pulse, PW_{OUT} , is zero. The input signal is rejected by input filter. Once the input signal pulse duration, PW_{IN} , exceeds input filter time, $t_{\text{FLT,IN}}$, the output pulse durations, PW_{OUT} , matches the input pulse durations, PW_{IN} . FAN7389 input filter time, $t_{\text{FLT,IN}}$, is about 250ns for the high- and low-side outputs.

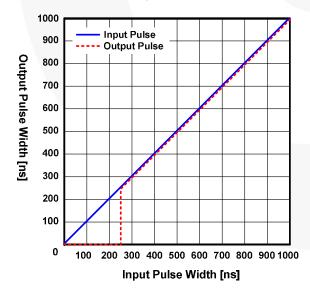


Figure 45.Input Filter Characteristic of Narrow ON

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Figure 46.24-Lead Small Outline Integrated Circuit (24-Wide Body SOIC)

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